

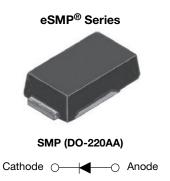
Vishay Semiconductors

AUTOMOTIVE

COMPLIANT HALOGEN

FREE

Ultrafast Rectifier, 2 A FRED Pt®



LINKS TO ADDITIONAL RESOURCES



| PRIMARY CHARACTERISTICS | | | | |
|----------------------------------|----------------|--|--|--|
| I _{F(AV)} | 2 A | | | |
| V_{R} | 100 V, 200 V | | | |
| V _F at I _F | 0.79 V | | | |
| I _{FSM} | 40 A | | | |
| t _{rr} (typ.) | 23 ns | | | |
| T _J max. | 175 °C | | | |
| Package | SMP (DO-220AA) | | | |
| Circuit configuration | Single | | | |

FEATURES

- Very low profile typical height of 1.0 mm
- · Ideal for automated placement
- · Low forward voltage drop, low power losses
- · Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- For PFC, CRM snubber operation
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

For use in high frequency, freewheeling, DC/DC converters, PFC, and in snubber industrial and automotive applications.

MECHANICAL DATA

Case: SMP (DO-220AA)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per

J-STD-002, meets JESD 201 class 2 whisker test

Polarity: color band denotes cathode end

| ABSOLUTE MAXIMUM RATINGS | | | | | | |
|---------------------------------------------|--------------|-----------------------------------|------------------------------------------|-------------|-------|--|
| PARAMETER | | SYMBOL | TEST CONDITIONS | VALUES | UNITS | |
| Dook ropotitivo roverso voltago | VS-2ENH01HM3 | W | | 100 | V | |
| Peak repetitive reverse voltage | VS-2ENH02HM3 | V_{RRM} | | 200 | , v | |
| Average rectified forward current | | I _{F(AV)} | T _C = 158 °C | 2 | Α | |
| Non-repetitive peak surge current | | I _{FSM} | T _J = 25 °C, 10 ms sine pulse | 40 | A | |
| Operating junction and storage temperatures | | T _J , T _{Stg} | | -55 to +175 | °C | |

| ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified) | | | | | | | |
|--------------------------------------------------------------------------------------|--------------|-------------------------|----------------------------------------------------------------|------|------|------|-------|
| PARAMETER | | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| Breakdown voltage, | VS-2ENH01HM3 | V _{BR} , | 1 100 | 100 | - | - | |
| blocking voltage VS-2ENH02HM3 | V_R | I _R = 100 μA | 200 | - | - | V | |
| Forward voltage | | V _F | I _F = 2 A | - | 0.94 | | 1.00 |
| | | | I _F = 2 A, T _J = 150 °C | - | 0.79 | | 0.84 |
| Reverse leakage current | | | V _R = V _R rated | - | - | 2 | μА |
| | | IR | T _J = 150 °C, V _R = V _R rated | - | - | 20 | |
| Junction capacitance | | C _T | V _R = 200 V | - | 8 | - | pF |

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| DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified) | | | | | | | |
|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------------------------------|------------------------------------------------------------------------|----------------------------------------------------------|------|------|------|---------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNITS |
| | | $I_F = 1.0 \text{ A}, dI_F/dt = 10$ | 0 A/μs, V _R = 30 V | - | 23 | - | |
| Reverse recovery time | | I _F = 0.5 A, I _R = 1 A, I _{rr} = 0.25 A | | - | - | 28 | 1 |
| neverse recovery time | verse recovery time t _{rr} | T _J = 25 °C | | - | 16 | - | ns - |
| | | T _J = 125 °C | | - | 25 | - | |
| Deel, we assume the state of th | T _J = 25 °C | $I_F = 2 A$ | - | 2.0 | - | Α | |
| Peak recovery current | eak recovery current I _{RRM} | T _J = 125 °C | dl _F /dt = 200 A/μs V _R = 100 V | - | 3.1 | - | A |
| Reverse recovery charge Q _{rr} | T _J = 25 °C | | - | 15 | - | nC | |
| heverse recovery charge | Q_{rr} | T _J = 125 °C | | - | 37 | - | |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | | |
|-----------------------------------------|----------------------|-----------------------------------|-------------------------------|------|-------|------|-------|
| PARAMETER | | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| Maximum junction and stora | ge temperature range | T _J , T _{Stg} | | -55 | - | 175 | °C |
| Thermal resistance, junction to mount | | R _{thJM} ⁽¹⁾ | Infinite heatsink | - | 7 | 9 | °C/W |
| Thermal resistance, junction to ambient | | R _{thJA} | PCB footprint 4.8 mm x 4.8 mm | - | 107 | - | C/VV |
| Approximate weight | | | | | 0.024 | | g |
| VS-2ENH01HM3 | | | Coop at the CMAD (DO 2004A) | 2H1 | | | |
| Marking device | VS-2ENH02HM3 | | Case style SMP (DO-220AA) | 2H2 | | | |

Note

⁽¹⁾ Thermal resistance junction to mount follows JEDEC® 51-14 transient dual interface test method (TDIM)

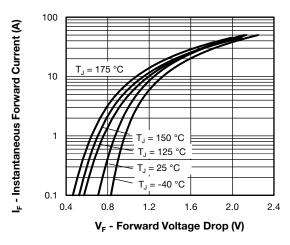


Fig. 1 - Typical Forward Voltage Drop Characteristics

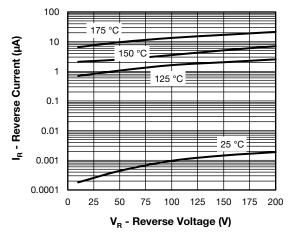


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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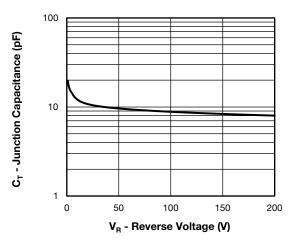


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

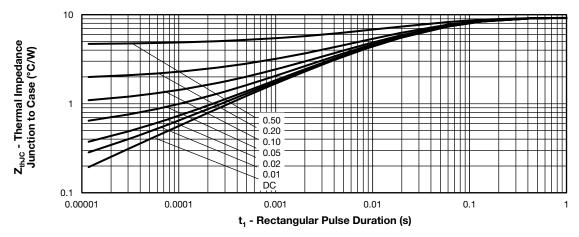


Fig. 4 - Transient Thermal Impedance, Junction to Case

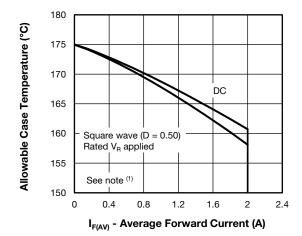


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

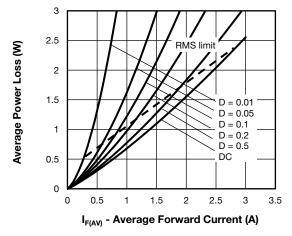


Fig. 6 - Forward Power Loss Characteristics

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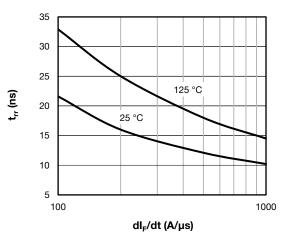


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

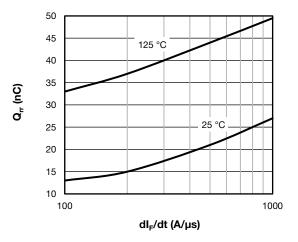
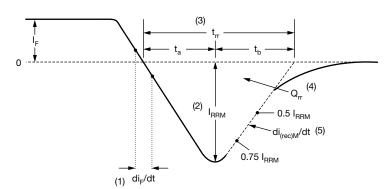


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

 $^{(1)}$ Formula used: T_C = T_J - (Pd + Pd_{REV}) x R_{thJC}; Pd = forward power loss = I_{F(AV)} x V_{FM} at (I_{F(AV)}/D) (see fig. 5); Pd_{REV} = inverse power loss = V_{R1} x I_R (1 - D); I_R at V_{R1} = rated V_R



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

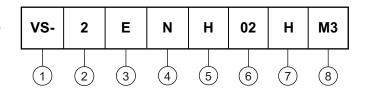
(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (2 = 2 A)

Circuit configuration:

E = single diode

4 - N = SMP package

Process type,

H = ultrafast recovery

6 - Voltage code (02 = 200 V)

7 - H = AEC-Q101 qualified

M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

| ORDERING INFORMATION (Example) | | | | | | |
|--------------------------------|------------------------|------------------------|------------------------------------|--|--|--|
| PREFERRED P/N | PREFERRED PACKAGE CODE | MINIMUM ORDER QUANTITY | PACKAGING DESCRIPTION | | | |
| VS-2ENH01HM3/84A | 84A | 3000 | 7" diameter plastic tape and reel | | | |
| VS-2ENH01HM3/85A | 85A | 10 000 | 13" diameter plastic tape and reel | | | |
| VS-2ENH02HM3/84A | 84A | 3000 | 7" diameter plastic tape and reel | | | |
| VS-2ENH02HM3/85A | 85A | 10 000 | 13" diameter plastic tape and reel | | | |

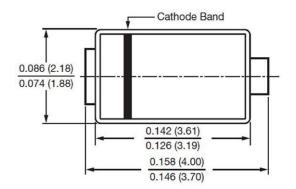
| LINKS TO RELATED DOCUMENTS | | | | |
|--------------------------------------------|--------------------------|--|--|--|
| Dimensions <u>www.vishay.com/doc?96547</u> | | | | |
| Part marking information | www.vishay.com/doc?96574 | | | |
| Packaging information | www.vishay.com/doc?88869 | | | |
| SPICE model | www.vishay.com/doc?96551 | | | |

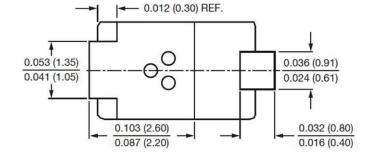


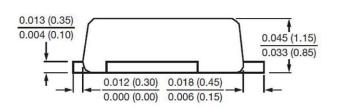
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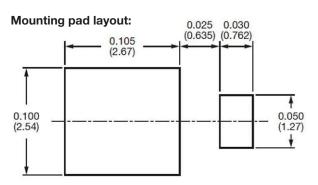
SMP (DO-220AA)

DIMENSIONS in inches (millimeters)











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